

1. Record Nr.	UNINA9910830721603321
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Titolo	Design and characterization of integrated varactors for RF applications [[electronic resource] /] / Inigo Gutierrez, Juan Melendez, Erik Hernandez
Pubbl/distr/stampa	Chichester, West Sussex, England ; ; Hoboken, NJ, : Wiley, c2006
ISBN	1-280-85476-6 9786610854769 0-470-03592-7 1-60119-377-7 0-470-03591-9
Descrizione fisica	1 online resource (182 p.)
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Disciplina	621.3815 621.381522
Soggetti	Varactors - Design and construction Radio capacitors - Design and construction Radio circuits - Design and construction Integrated circuits - Design and construction
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references and index.
Nota di contenuto	Design and Characterization of Integrated Varactors for RF Applications; Contents; List of Figures; List of Tables; Preface; Acknowledgements; 1 Introduction; 1.1 Passive Elements; 1.2 Figures of Merit of Varactors; 1.2.1 Quality Factor; 1.2.2 Tuning Range; 1.2.3 Self-resonant Frequency(fR); 1.2.4 Effective Silicon Area; 1.2.5 Absolute Capacity Value; 1.3 Principal Types of Varactor Manufacture; 1.3.1 Discrete Varactors; 1.3.2 MEMS Varactors; 1.3.3 BST Varactors; 1.3.4 Integrated Varactors using Standard Technologies; References; 2 PN-junction Varactors 2.1 The Operating Principle of a PN-junction Varactor2.1.1 Electrical Phenomena in a PN-junction Varactor; 2.2 Different Architectures of PN-junction Varactors; 2.2.1 Different Configurations of PN-junction

Varactors; 2.3 Influence of Bias Voltage on the Behaviour of a PN-junction Varactor; 2.4 Influence of Geometric Parameters on the Behaviour of a PN-junction Varactor; 2.4.1 Influence in the Variation of the Number of Islands; 2.4.2 Influence of the Size of the Islands; 2.4.3 Influence of the Distance Between Islands; 2.4.4 Variation of the Size of the N Well

2.5 Influence of the Working Frequency on the Results 2.5.1 Influence of the Frequency on the Quality of a Varactor; 2.5.2 Influence of the Frequency on the Capacitance of a Varactor; 2.6 Comparison Between the Different Types of PN-junction Varactors; 2.6.1 Comparison According to the Effective Silicon Area; 2.6.2 Comparison According to the Quality Factor; References; 3 MOS Varactors; 3.1 Operating Principles of an NMOS Varactor; 3.1.1 Operating Ranges of the NMOS Varactor; 3.1.2 Electrical Phenomena of an NMOS Varactor in Accumulation Mode

3.1.3 Electrical Phenomena of an NMOS Varactor in Depletion Mode 3.2 NMOS Varactors; 3.2.1 Operating Ranges of the NMOS Varactor; 3.3 Influence of the Operating Mode on an NMOS Varactor; 3.4 Influence of Bias Voltage on the Behaviour of an NMOS Accumulation Varactor; 3.5 Influence of Geometric Parameters on the Behaviour of an NMOS Varactor; 3.5.1 Influence of the Variation of the Varactor Size; 3.5.2 Influence of the Varactor Gate Length on its Performance; 3.5.3 Influence of the Varactor Gate Width on its Performance; 3.6 Influence of the Working Frequency on the Results; References

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4.7.1 Error Introduced by Positioning the Test Probes on the Pads

Sommario/riassunto

Varactors are passive semiconductor devices used in electronic circuits, as a voltage-controlled way of storing energy in order to boost the amount of electric charge produced. In the past, the use of low-cost fabrication processes such as complementary metal oxide semiconductor (CMOS) and silicon germanium (SiGe) were kept for integrated circuits working in frequency ranges below the GHz. Now, the increased working frequency of radio frequency integrated circuits (RF ICs) for communication devices, and the trend of system-on-chip technology, has pushed the requirements of varactors to the lim